

# EC2645TTS-81.250M TR [↗](#)



## ITEM DESCRIPTION

Quartz Crystal Clock Oscillators XO (SPXO) LVCMOS (CMOS) 3.3Vdc 4 Pad 5.0mm x 7.0mm Ceramic Surface Mount (SMD) 81.250MHz  $\pm 50$ ppm  $-10^{\circ}\text{C}$  to  $+70^{\circ}\text{C}$

## ELECTRICAL SPECIFICATIONS

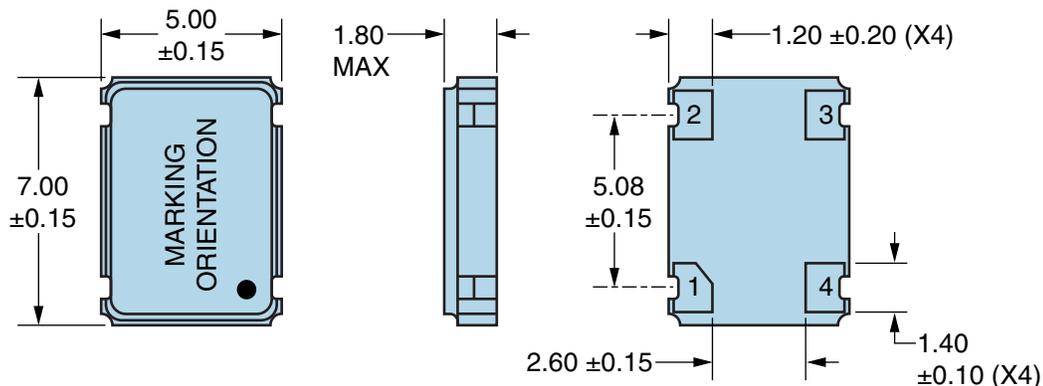
Nominal Frequency	81.250MHz
Frequency Tolerance/Stability	$\pm 50$ ppm Maximum (Inclusive of all conditions: Calibration Tolerance at $25^{\circ}\text{C}$ , Frequency Stability over the Operating Temperature Range, Supply Voltage Change, Output Load Change, First Year Aging at $25^{\circ}\text{C}$ , Shock, and Vibration)
Aging at $25^{\circ}\text{C}$	$\pm 5$ ppm/year Maximum
Operating Temperature Range	$-10^{\circ}\text{C}$ to $+70^{\circ}\text{C}$
Supply Voltage	3.3Vdc $\pm 10\%$
Input Current	40mA Maximum
Output Voltage Logic High (Voh)	90% of Vdd Minimum (IOH= $-8$ mA)
Output Voltage Logic Low (Vol)	10% of Vdd Maximum (IOL= $+8$ mA)
Rise/Fall Time	3nSec Maximum (Measured at 20% to 80% of waveform)
Duty Cycle	50 $\pm 5$ (%) (Measured at 50% of waveform)
Load Drive Capability	15pF Maximum
Output Logic Type	CMOS
Pin 1 Connection	Tri-State (High Impedance)
Output Control Input Voltage Logic High (Vih)	70% of Vdd Minimum or No Connect to Enable Output
Output Control Input Voltage Logic Low (Vil)	30% of Vdd Maximum to Disable Output (High Impedance)
Standby Current	10 $\mu$ A Maximum (Disabled Output: High Impedance)
RMS Phase Jitter	1pSec Maximum (12kHz to 20MHz offset frequency)
Start Up Time	10mSec Maximum
Storage Temperature Range	$-55^{\circ}\text{C}$ to $+125^{\circ}\text{C}$

## ENVIRONMENTAL & MECHANICAL SPECIFICATIONS

ESD Susceptibility	MIL-STD-883, Method 3015, Class 1, HBM: 1500V
Fine Leak Test	MIL-STD-883, Method 1014, Condition A
Flammability	UL94-V0
Gross Leak Test	MIL-STD-883, Method 1014, Condition C
Mechanical Shock	MIL-STD-883, Method 2002, Condition B
Moisture Resistance	MIL-STD-883, Method 1004
Moisture Sensitivity	J-STD-020, MSL 1
Resistance to Soldering Heat	MIL-STD-202, Method 210, Condition K
Resistance to Solvents	MIL-STD-202, Method 215
Solderability	MIL-STD-883, Method 2003
Temperature Cycling	MIL-STD-883, Method 1010, Condition B
Vibration	MIL-STD-883, Method 2007, Condition A

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## MECHANICAL DIMENSIONS (all dimensions in millimeters)



PIN	CONNECTION
1	Tri-State
2	Case/Ground
3	Output
4	Supply Voltage

LINE	MARKING
1	ECLIPTEK
2	81.250M
3	XXXXXX XXXXXX=Ecliptek Manufacturing Identifier

## Suggested Solder Pad Layout

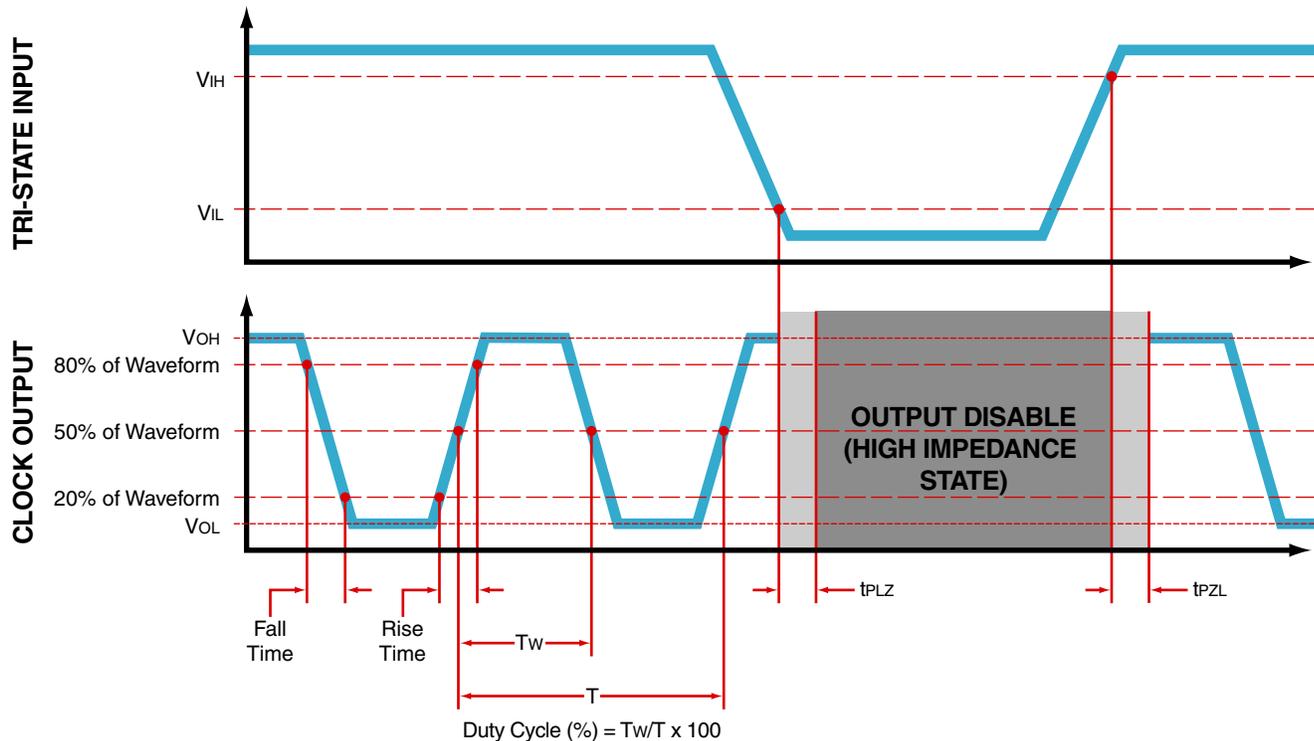
All Dimensions in Millimeters



All Tolerances are  $\pm 0.1$

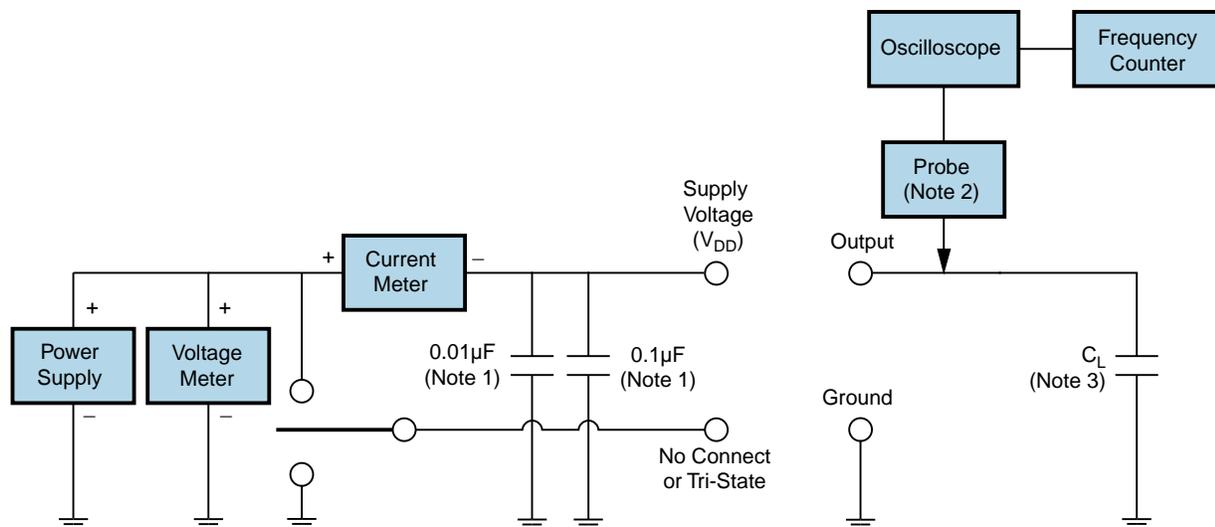
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## OUTPUT WAVEFORM & TIMING DIAGRAM



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## Test Circuit for CMOS Output



Note 1: An external  $0.1\mu\text{F}$  low frequency tantalum bypass capacitor in parallel with a  $0.01\mu\text{F}$  high frequency ceramic bypass capacitor close to the package ground and  $V_{DD}$  pin is required.

Note 2: A low capacitance ( $<12\text{pF}$ ), 10X attenuation factor, high impedance ( $>10\text{Mohms}$ ), and high bandwidth ( $>300\text{MHz}$ ) passive probe is recommended.

Note 3: Capacitance value  $C_L$  includes sum of all probe and fixture capacitance.

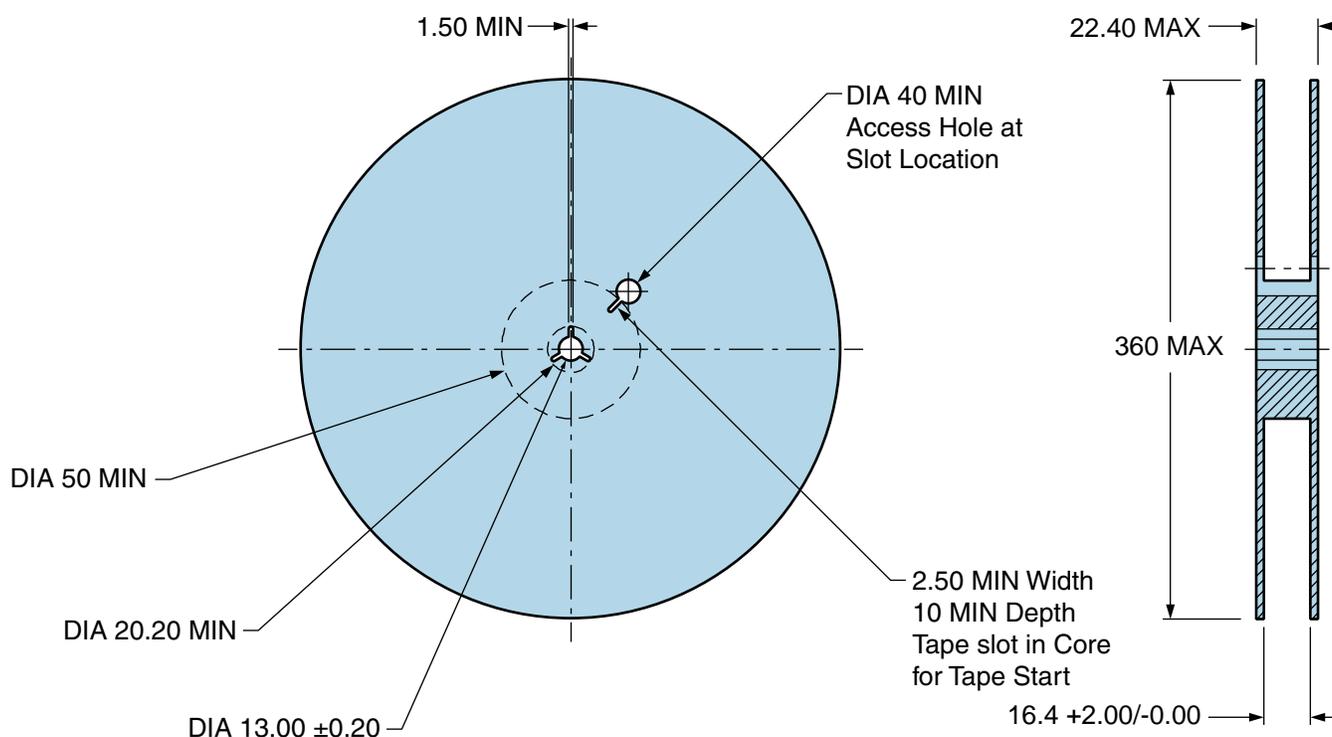
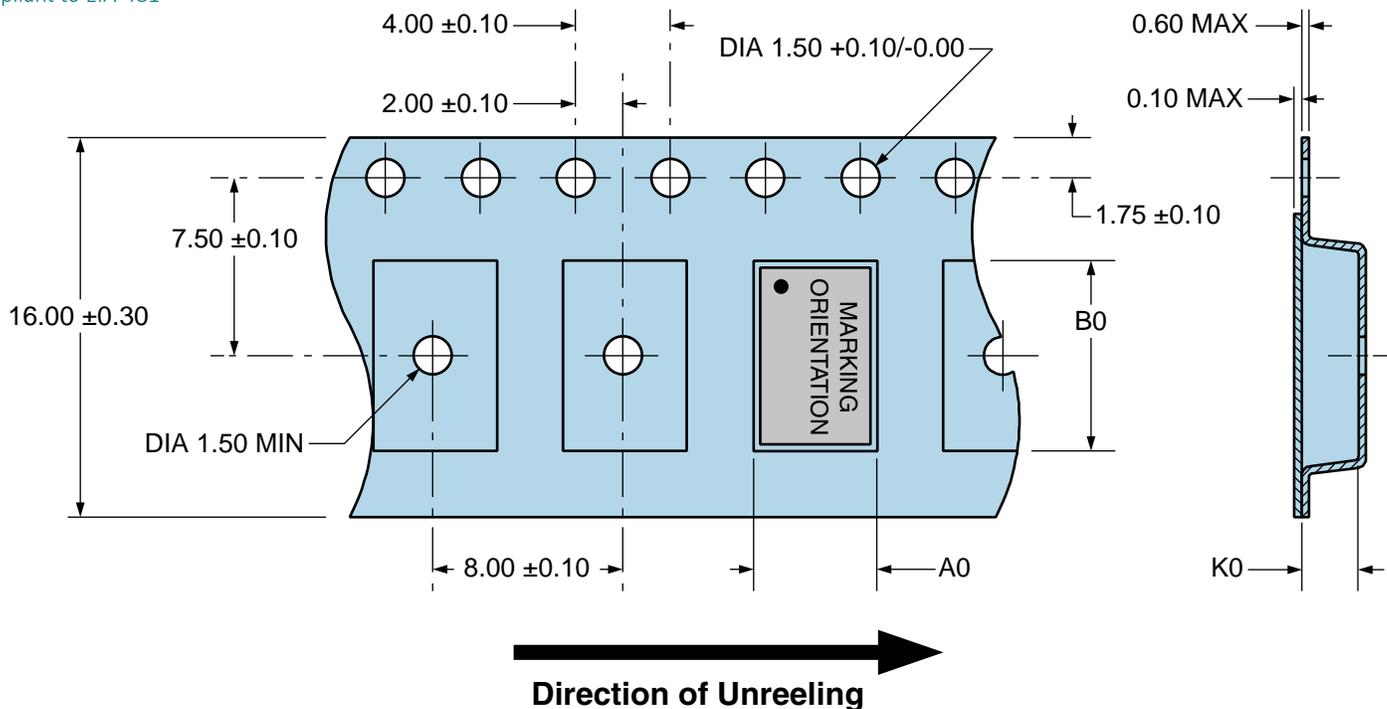
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## Tape & Reel Dimensions

Quantity Per Reel: 1,000 units

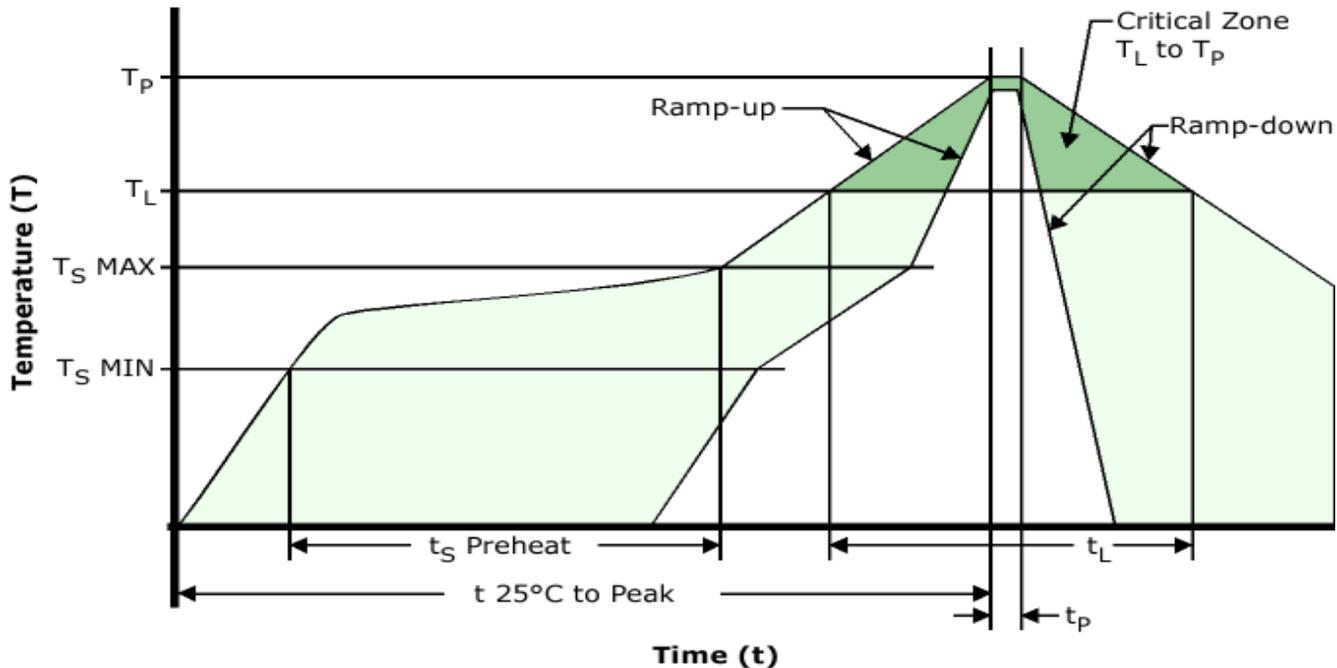
All Dimensions in Millimeters

Compliant to EIA-481



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## Recommended Solder Reflow Methods

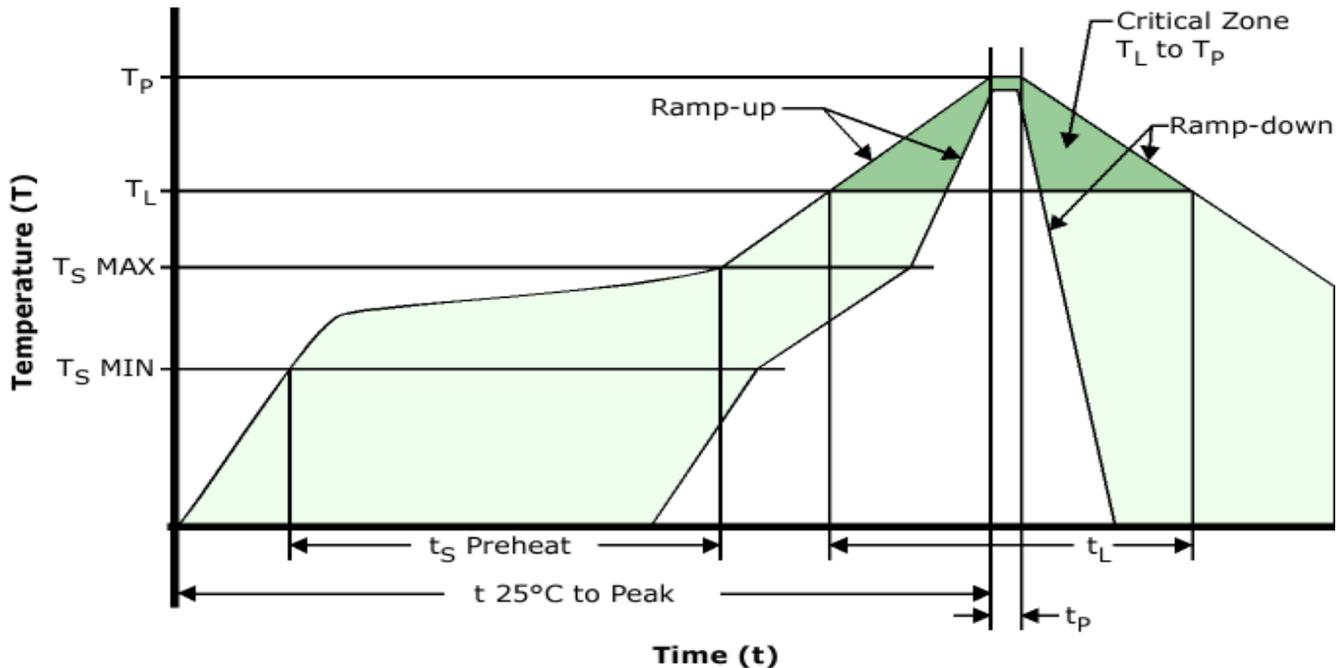


## High Temperature Infrared/Convection

$T_S$ MAX to $T_L$ (Ramp-up Rate)	3°C/Second Maximum
<b>Preheat</b>	
- Temperature Minimum ( $T_S$ MIN)	150°C
- Temperature Typical ( $T_S$ TYP)	175°C
- Temperature Maximum ( $T_S$ MAX)	200°C
- Time ( $t_s$ MIN)	60 - 180 Seconds
<b>Ramp-up Rate (<math>T_L</math> to <math>T_P</math>)</b>	3°C/Second Maximum
<b>Time Maintained Above:</b>	
- Temperature ( $T_L$ )	217°C
- Time ( $t_L$ )	60 - 150 Seconds
<b>Peak Temperature (<math>T_P</math>)</b>	260°C Maximum for 10 Seconds Maximum
<b>Target Peak Temperature (<math>T_P</math> Target)</b>	250°C +0/-5°C
<b>Time within 5°C of actual peak (<math>t_p</math>)</b>	20 - 40 Seconds
<b>Ramp-down Rate</b>	6°C/Second Maximum
<b>Time 25°C to Peak Temperature (t)</b>	8 Minutes Maximum
<b>Moisture Sensitivity Level</b>	Level 1
<b>Additional Notes</b>	Temperatures shown are applied to body of device.

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## Recommended Solder Reflow Methods



### Low Temperature Infrared/Convection 240°C

$T_S \text{ MAX}$  to  $T_L$  (Ramp-up Rate) 5°C/Second Maximum

#### Preheat

- Temperature Minimum ( $T_S \text{ MIN}$ ) N/A  
 - Temperature Typical ( $T_S \text{ TYP}$ ) 150°C  
 - Temperature Maximum ( $T_S \text{ MAX}$ ) N/A  
 - Time ( $t_s \text{ MIN}$ ) 60 - 120 Seconds

Ramp-up Rate ( $T_L$  to  $T_P$ ) 5°C/Second Maximum

#### Time Maintained Above:

- Temperature ( $T_L$ ) 150°C  
 - Time ( $t_L$ ) 200 Seconds Maximum

Peak Temperature ( $T_P$ ) 240°C Maximum

Target Peak Temperature ( $T_P \text{ Target}$ ) 240°C Maximum 2 Times / 230°C Maximum 1 Time

Time within 5°C of actual peak ( $t_p$ ) 10 Seconds Maximum 2 Times / 80 Seconds Maximum 1 Time

Ramp-down Rate 5°C/Second Maximum

Time 25°C to Peak Temperature ( $t$ ) N/A

Moisture Sensitivity Level Level 1

Additional Notes Temperatures shown are applied to body of device.

### Low Temperature Manual Soldering

185°C Maximum for 10 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)

### High Temperature Manual Soldering

260°C Maximum for 5 Seconds Maximum, 2 times Maximum. (Temperatures shown are applied to body of device.)